

R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-Spice, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-Spice Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION

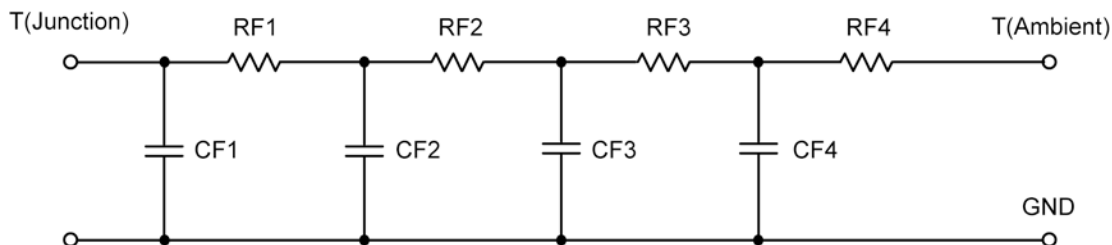


R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	5.2636	N/A	11.2331
RT2	32.2775	N/A	7.2014
RT3	18.4920	N/A	502.7000 m
RT4	48.9669	N/A	19.0628
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	1.4191 m	N/A	9.2099 m
CT2	56.5003 m	N/A	1.3529 m
CT3	11.9074 m	N/A	8.2212
CT4	1.7733	N/A	54.6991 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.



R-C THERMAL MODEL FOR FILTER CONFIGURATION



R-C VALUES FOR FILTER CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	4.2231	N/A	8.7939
RF2	23.6271	N/A	12.3196
RF3	30.8934	N/A	9.5891
RF4	46.2564	N/A	7.2974
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	791.1520 u	N/A	1.1401 m
CF2	6.6067 m	N/A	5.9885 m
CF3	49.0098 m	N/A	48.9471 m
CF4	1.8673	N/A	8.1118 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

